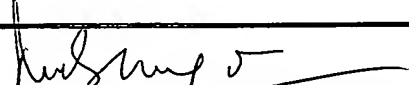


Substitute for form 1449/PTO (Revised 04/2003)  <b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b> (Use as many sheets as necessary)				<b>Complete if Known</b>	
				Application Number	To Be Assigned
				Filing Date	Concurrently Herewith
				First Named Inventor	David A. Beauchaine, et al.
				Group Art Unit	
Examiner Name					
Sheet	1	of	1	Attorney Docket Number	039035/273763
<b>U. S. PATENT DOCUMENTS</b>					
Examiner Initials*	Cite No.	Document Number Number - Kind Code (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages of Relevant Figures Appear
L	1	US-2002/0119641 A1	08-29-2002	Zehavi, et al.	
L	2	US-2002/0170487 A1	11-21-2002	Zehavi, et al.	
L	3	US-6,504,233 B1	01-07-2003	Gorczyca, et al.	
L	4	US-6,617,225 B2	09-09-2003	Boyle, et al.	
<b>OTHER DOCUMENTS</b>					
Examiner Initials	Cite No.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.			English Language Translation Attached
L	5	Asahi Glass Electronic Materials, Roiceram-HS - Ultra High Purity Silicon Carbide, Materials Brochure, undated.			
L	6	SATOSHI KAWAMOTO, FUMITOMO KAWAHARA, TROY COLLARD, Semiconductor Fabtech - 12 <sup>th</sup> Edition, SiC Applications for Semiconductor Manufacturing, undated.			
Examiner Signature				Date Considered	02/20/06

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